

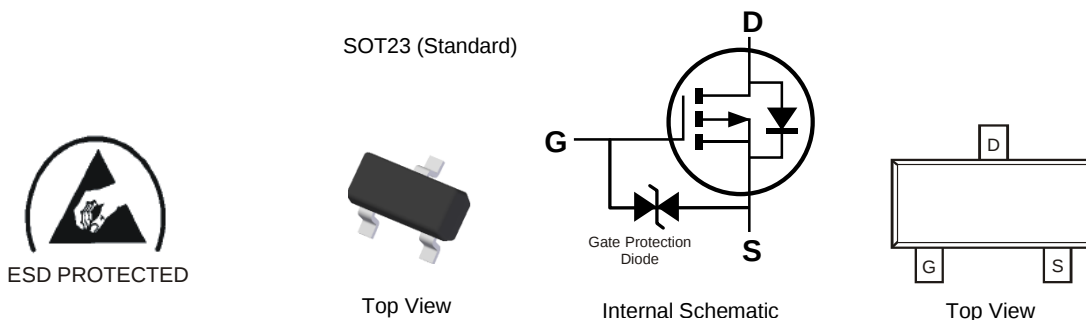
Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/contact-us) or your local Diodes representative.**

<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

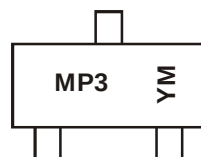


Ordering Information (Notes 4 & 5)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMP2035U-7	SOT23 (Standard)	3,000	7" Tape & Reel
DMP2035U-13	SOT23 (Standard)	10,000	13" Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
 5. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V_{GSS} rating (given on page 2) can be applied.

Marking Information



MP3 = Product Type Marking Code
YM = Date Code Marking
Y or $\bar{Y}$ = Year (ex: M = 2025)
M = Month (ex: 9 = September)

Date Code Key

Year	2011	...	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	Y	...	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 8) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-4.9 -4.0	A
Pulsed Drain Current (Note 8)			I _{DM}	-24	A
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	-1.2	A
Pulsed Body Diode Forward Current (Note 10)			I _{SM}	-24	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	0.81	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	153.5	°C/W
Total Power Dissipation (Note 7)	P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 7)	R _{θJA}	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current, T _J = +25°C	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	-0.7	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	23	35	mΩ	V _{GS} = -4.5V, I _D = -4.0A
			30	45		V _{GS} = -2.5V, I _D = -4.0A
			41	62		V _{GS} = -1.8V, I _D = -2.0A
			—	—		V _{GS} = -1.8V, I _D = -2.0A
Forward Transfer Admittance	Y _{FS}	—	14	—	s	V _{DS} = -5V, I _D = -4A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	1,610	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	157	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	145	—	pF	
Gate Resistance	R _g	—	9.45	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	15.4	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4A
Gate-Source Charge	Q _{gs}	—	2.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	3.3	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	16.8	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _g = 6.0Ω, I _D = -1A
Turn-On Rise Time	t _r	—	12.4	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	94.1	—	ns	
Turn-Off Fall Time	t _f	—	42.4	—	ns	

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 25mm x 25mm square copper plate.
 8. Repetitive rating, pulse width limited by junction temperature.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.

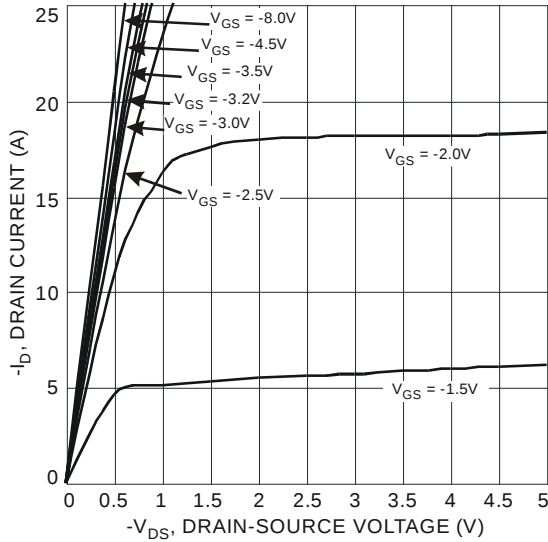


Fig. 1 Typical Output Characteristic

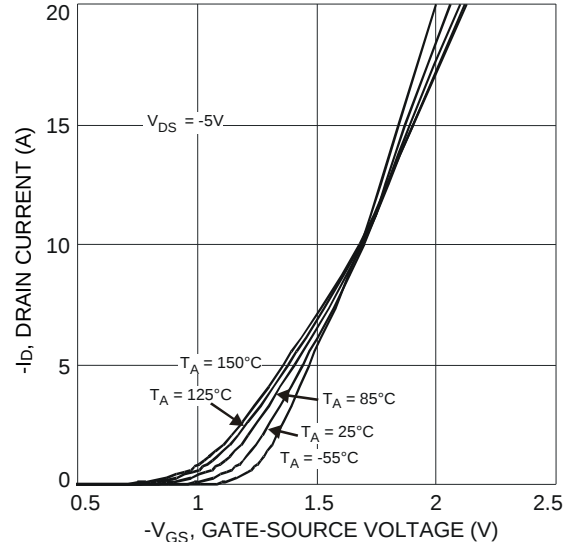


Fig. 2 Typical Transfer Characteristic

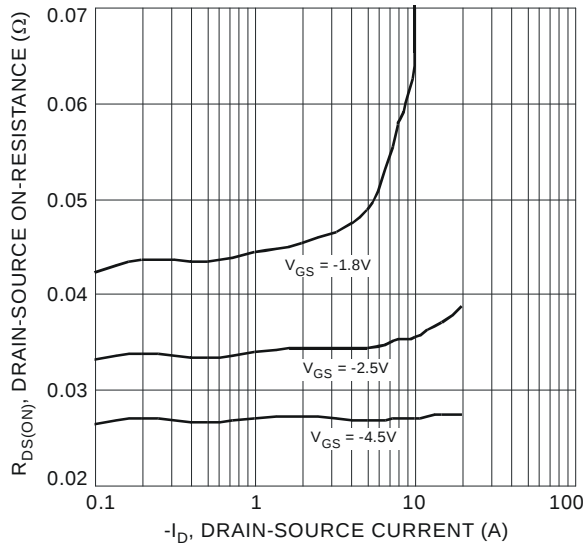


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

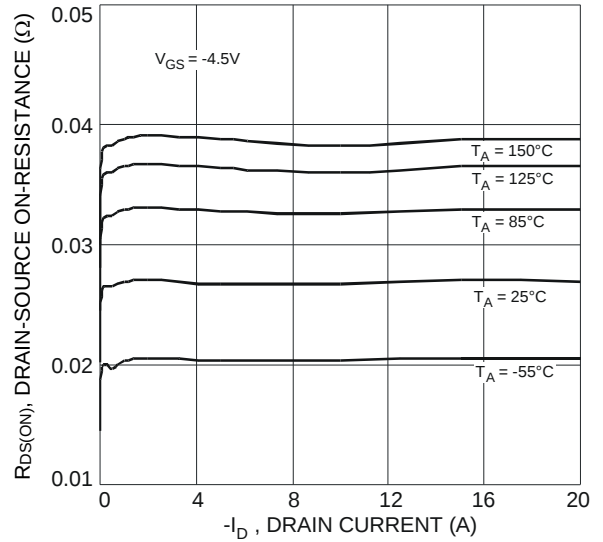


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

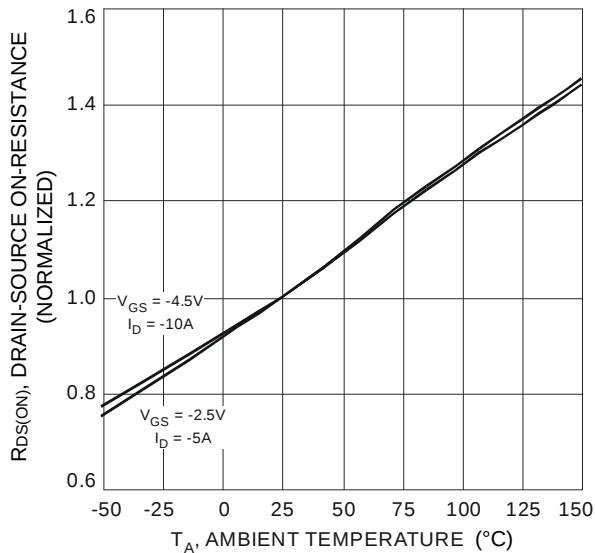


Fig. 5 On-Resistance Variation with Temperature

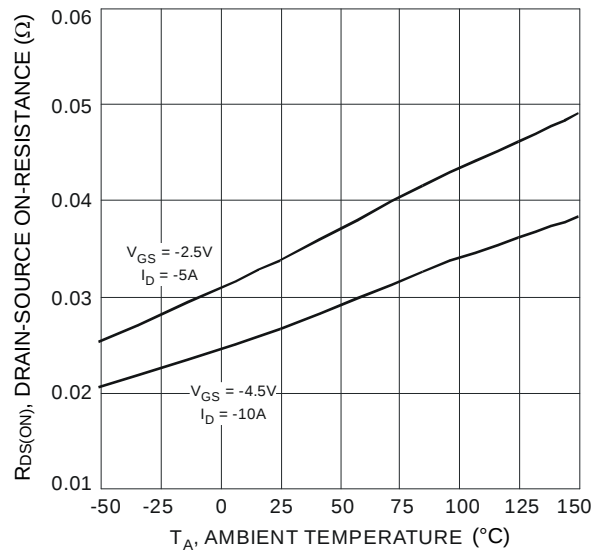


Fig. 6 On-Resistance Variation with Temperature

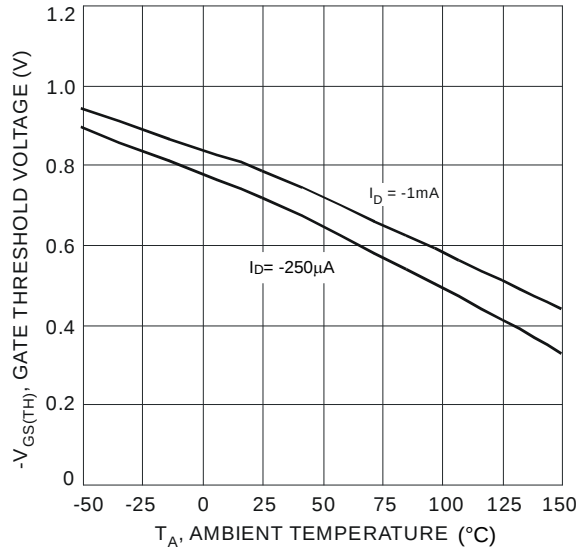


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

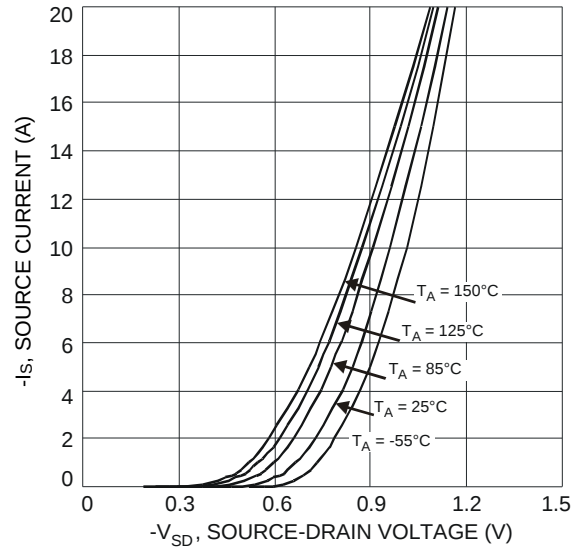


Fig. 8 Diode Forward Voltage vs. Current

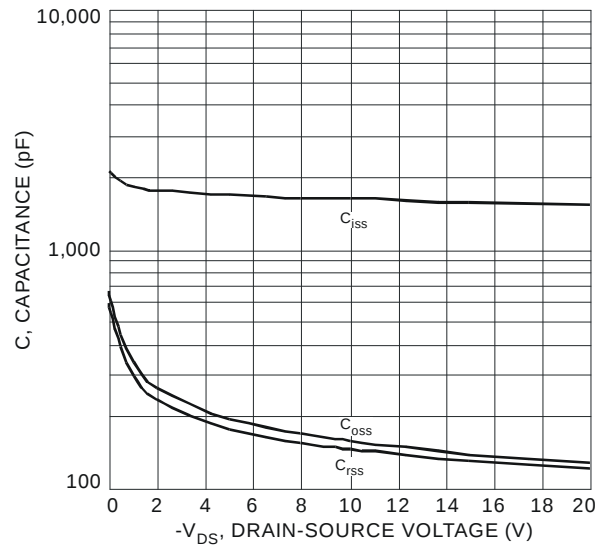


Fig. 9 Typical Total Capacitance

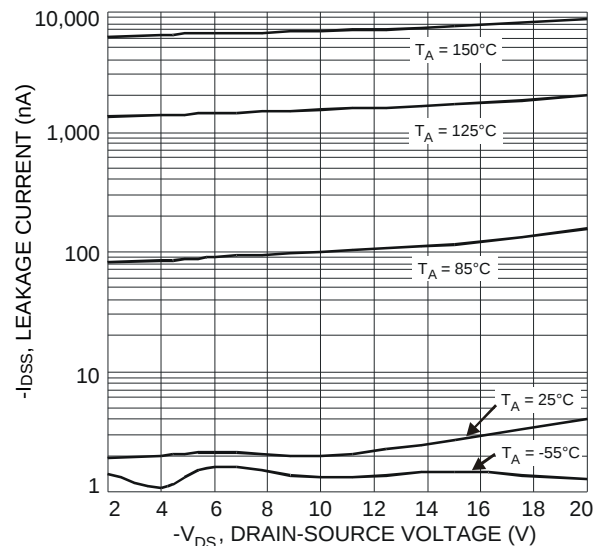


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

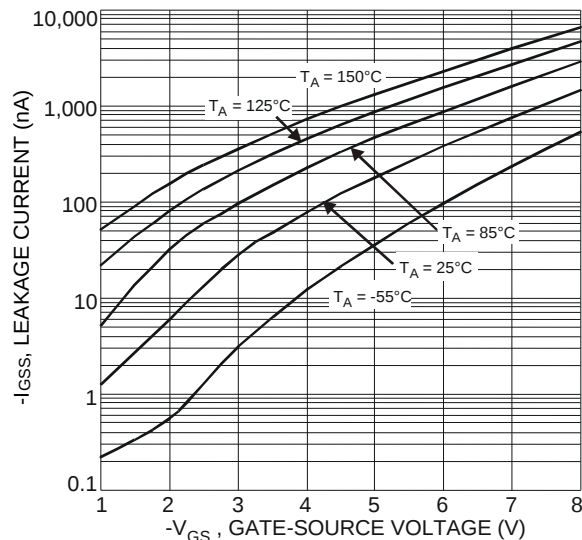


Fig. 11 Gate-Source Leakage Current vs. Voltage

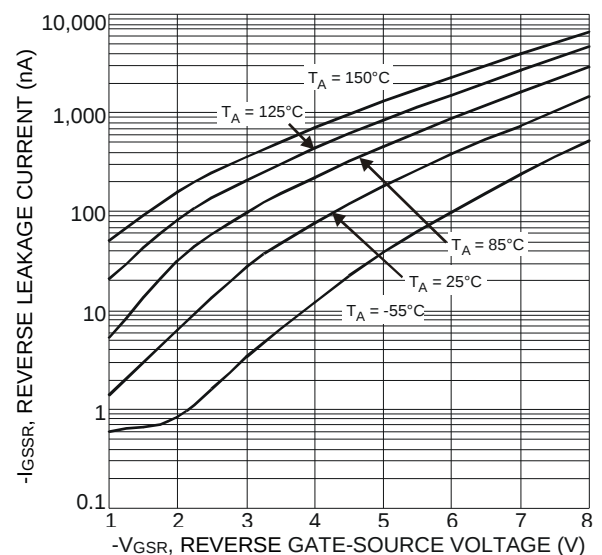
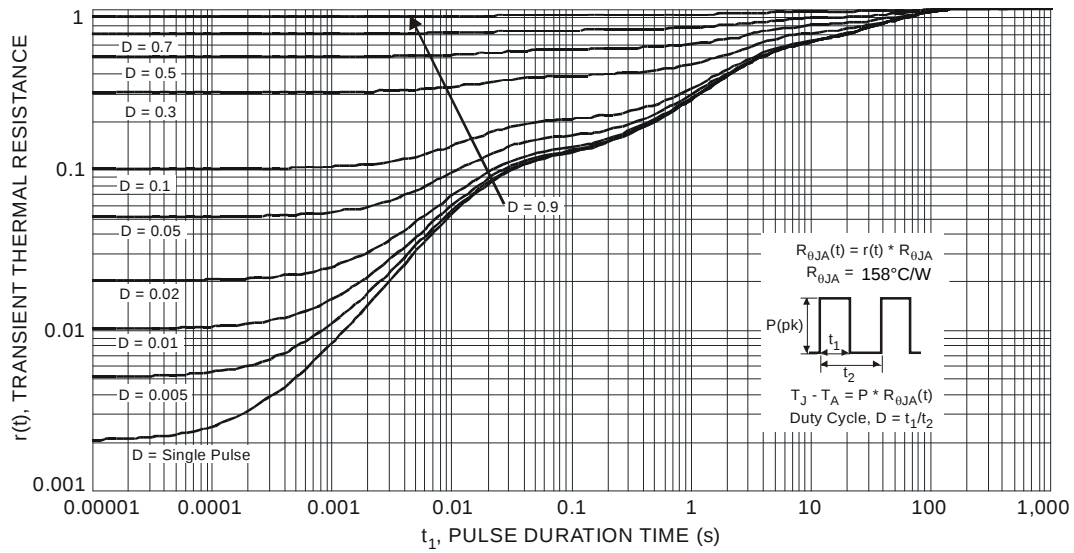
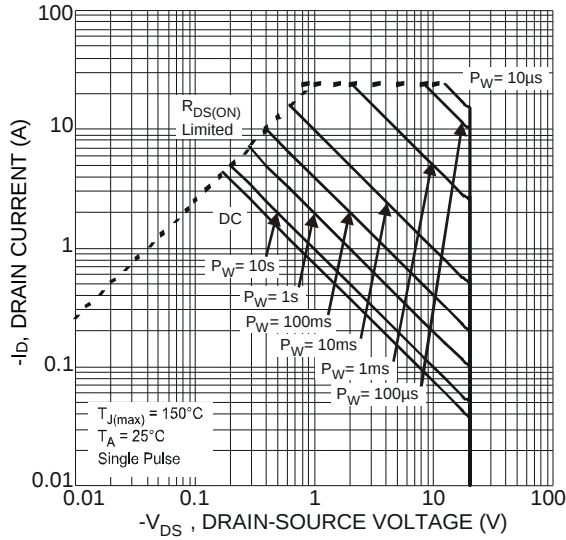


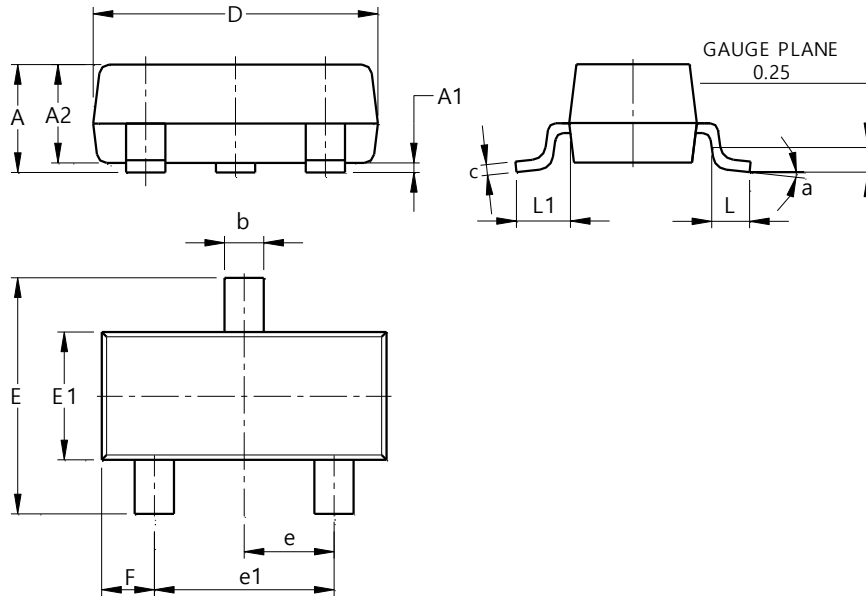
Fig. 12 Reverse Gate-Source Leakage Current vs. Voltage



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)

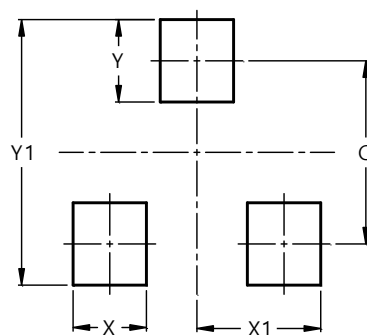


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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